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**Tailoring the properties of two dimensional molybdenum disulfide** SAIFUL I. KHONDAKER, MUHAMMAD R. ISLAM, NARAE KANG, UDAI BHANU, HARI P. PAUDEL, MIKHAIL EREMENTCHOUK, LAURENE TETARD, MICHAEL N. LEUENBERGER, NanoScience Technology Center and Department of Physics, University of Central Florida — The ability to tailor the properties of a material is essential to optimize device functionality. In this talk, I will present evidence that the electrical and optical properties two-dimensional (2D) molybdenum disulfide ( $\text{MoS}_2$ ) can be tuned by controlled exposure to oxygen plasma. We find that the mobility, on-current and resistance of 2D  $\text{MoS}_2$  FETs vary exponentially by up to four orders of magnitude with respect to the plasma exposure time. Photoluminescence (PL) study show a decrease of PL intensity leading a complete quenching. Raman studies show a significant decrease of intensity of  $\text{MoS}_2$  peaks with the creation of new oxidation induced peak, while X-ray photoelectron spectroscopy (XPS) study show peaks associated with  $\text{MoO}_3$  after plasma exposure. We suggest that during exposure to oxygen plasma, the energetic oxygen molecules interact with  $\text{MoS}_2$  and create  $\text{MoO}_3$  rich defected-regions, which are insulating.  $\text{MoO}_3$  defected-regions act as a tunnel barrier for the injected conduction electrons, giving rise to the exponential increase in resistivity as a function of plasma exposure time. Bandstructure calculation shows that the PL quenching upon plasma exposure is due to the creation of  $\text{MoO}_3$  defected-regions which causes a direct to indirect bandgap transition in monolayer  $\text{MoS}_2$ .

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